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Disorder-driven magnetic field-dependent phases in an organic conductor

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We report inter-plane (R_{zz}) electrical transport measurements in the τ-phase series of organic conductors at very high magnetic fields. In the field range between 36 and 60 T R_{zz} shows a very hysteretic first order phase transition from metallic to an insulating state. This transition does not affect the Shubnikov-de-Haas oscillations associated with the two-dimensional (2D) Fermi surface. We argue that this transition originates from inter-plane disorder which gives rise to incoherent transport along the least conducting axis. We conclude that this system becomes a strictly 2D Fermi-liquid at high magnetic fields.

Disorder and complexity play important roles in many systems of current interest in condensed matter physics. In colossal magnetoresistance (CMR) systems[1] such as the manganites, magnetic disorder and inhomogeneity lead to dramatic changes in resistivity with magnetic field and temperature[2]. In organic conductors with complex, polymeric anions and cation end-groups, conformational disorder may lead to insulating behavior, associated to the localization of the electron states, and to weak ferromagnetism even in the absence of magnetic ions [3, 4]. As recent reviews have shown[5, 6], important mechanisms and physical properties are shared by organic and inorganic materials, particularly in layered, anisotropic systems. Recently "bad metal" (i.e. $k_F\ell \approx 1$) characteristics have been reported in a transition metal oxide (TMO) that paradoxically, exhibits Shubnikov de Haas oscillations ($\omega_c\tau \gg 1$) at low temperatures[7]. This also appears to be the case of the τ-phase organic conductor series presented in this Letter, where disorder, magnetism, and high anisotropy play important roles in determining the ground state properties of layered materials.

Our main experimental result is the universal behavior of the inter-plane resistance (R_{zz}) of three isostructural members of the τ-phase class of organic conductors[8, 9, 10, 11, 12] in very high ($B > 36T$) magnetic fields. Here we find a first order metal-to-insulator transition in R_{zz} above a temperature-dependent threshold field B_{th}. An overview of the field-temperature phase diagram of these materials is shown in Fig. 1. What is remarkable about this transition is that unlike the well-known field induced spin density wave transitions in quasi-one dimensional organic conductors[13], where an orbital Fermi surface nesting effect is involved[14], B_{th} appears to be only weakly dependent on magnetic field direction. Hence the mechanism that drives the transition at B_{th} may be primarily isotropic, or Zeeman-like in origin, and we must look for other physical characteristics of these materials which cause this dramatic transition to the insulating state.

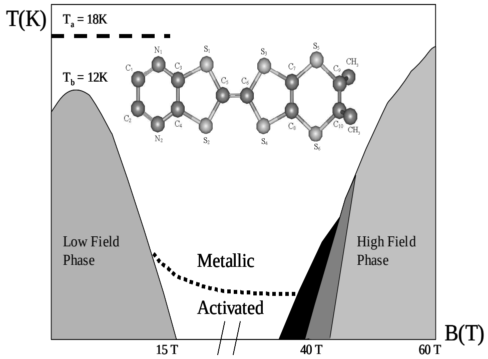

FIG. 1: Schematic phase diagram of the τ-phase organic conductors based on the DMEDT-TTF donor molecule (inset). The low and intermediate field phase boundaries are obtained from temperature dependent resistance measurements. (See text for details.) Between 12 and 40 T quantum oscillations characteristic of a 2D Fermi surface are observed. The threshold fields B_{th} for the high field phase boundaries are based on pulsed field magnetoresistance data for (1) $\tau(r)$-$AuBr_2$, (2) τ-$AuBr_2$, (3) τ-AuI_2, low to high, respectively.

The complexity and structure of the τ-phase unit cell is unique amongst the general class of charge transfer salts (CTS)[15]. Three forms of the τ-phase materials have been studied in the present work. The formula unit for the material we have most extensively studied[18] (hereafter τ-$AuBr_2$) is τ-(P-(S,S)-DMEDT-TTF$)_2(AuBr_2)(AuBr_2)_y$ (where $y \approx 0.75$). The iodine anion system τ-(P-(S,S)-DMEDT-TTF$)_2(AuI_2)(AuI_2)_y$ (hereafter τ-(AuI_2) is also investigated in this work, as is a disordered racemic system with $AuBr_2$(see below). The DMEDT-TTF donor is shown in the inset of Fig. 1. Unlike conventional CTS materials where the charge transfer is 2:1, here it is 2:(1+y) and the anions occupy two different sites in the unit cell: for instance the $AuBr_2$ anion sits at the center of a square array of DMEDT-TTF donors in the conducting layer[10], and the $(AuBr_2)_y$ anions are arranged in the inter-layer planes where their orientation alternates by 90^o between successive layers. Since DMEDT-TTF is asymmetric, the donor stacking involves alternating directions within the donor layer. Hence, due to the very low symmetry of the donor and anion arrangement, four donor layers are necessary to complete the unit cell[11], and the result is an unusually large inter-planar dimension: $(a, b, c \approx 7.4, 7.4, 68\ \mathring{A})$. Further disorder, beyond the non-stoichiometry of the anion structure, can be introduced into the τ-phase system with a racemic mixture of two different isomers(*R,R* and *S,S*) of the donor molecules[16, 17]. In general the ratio of the two isomers is not fifty-fifty, and this enhances the disorder over crystals containing the pure (*R,R* or *S,S*) arrangements. The racemic system studied in the present work is τ-(P-(r)-DMEDT-TTF)$_2$(AuBr$_2$)(AuBr$_2$)$_y$ (hereafter τ(r)-AuBr$_2$).

In this investigation, single crystals of τ-phase materials (square plates of average size $1 \times 1 \times 0.2\ mm^3$) were grown by electrochemical methods. All measurements were four-terminal, inter-plane resistance measurements with current values between 50 nA and 300 μA. Electrical contact was made to the samples with 25 micron gold wires connected with carbon or silver paint. Experiments were carried out at the National High Magnetic Field Laboratory (NHMFL) DC field facilities in Tallahassee with standard low frequency AC techniques, and at NHMFL-Los Alamos with pulsed magnets. For pulsed field measurements, forward and reverse DC current traces were taken to remove the induced *emf* signals.

The temperature dependence of the inter-plane resistance for different magnetic fields for the three τ-phase materials studied is shown in Fig. 2. The following convention for presentation order is used in the figures: $\tau-(r)-AuBr_2$, $\tau-AuBr_2$, and $\tau-AuI_2$ to represent the level of disorder and/or anion radii (where Br is smaller than I) respectively. Although the data in Fig. 2 differs in emphasis of field, temperature, and material studied, there are universal features that arise in all cases, as reflected in the phase diagram of Fig. 1. The inter-plane resistance R_{zz} increases monotonically with decreasing temperature, but there is a characteristic temperature labelled $T_a \approx 18K$ where the resistance appears to be magnetic field independent. (The magnetoresistance is positive above T_a, and negative below T_a.) At lower temperatures an anomaly (plateau or kink) appears in R_{zz} for zero field at $T_b \approx 12K$. The detailed structure of the feature in R_{zz} at T_b quickly disappears with increasing magnetic field. If the change of slope in the temperature dependence is monitored, T_b first increases slightly, then decreases with increasing field. At fields greater than 5 T, the point where dR/dT changes sign can be easily determined. In all samples, at all fields, dR/dT eventually becomes negative with decreasing temperature. Both T_a and T_b are shown in Fig. 1 as derived from these observations in the field range 0 to 27 T.

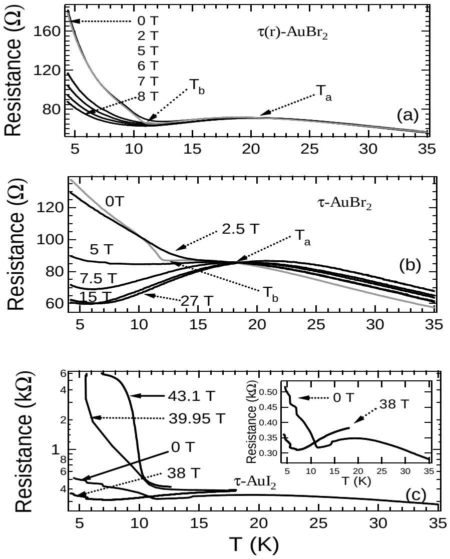

FIG. 2: The temperature dependence of the resistance of the three τ-phase materials for different magnetic fields. (T_a and T_b are defined in the text.) a) τ(r)-AuBr$_2$, b) τ-AuBr$_2$, c) τ-AuI$_2$. Inset: expanded view of low resistance traces.

The high magnetic field dependence of R_{zz} of the τ-phase materials has been investigated in a DC hybrid magnet up to 45 T (Fig. 3), and in pulsed fields(6 ms rise-time) up to 60 T (Fig. 4). In all cases a transition between a metallic state and a highly insulating state is observed in R_{zz} at a threshold field B_{th}. In Fig. 5 details of the Shubnikov-de Haas (SdH) effect are shown for representative low temperature hybrid data. (In the present work SdH frequencies were observed over a range of 500 to 800 T, depending on field orientation. See also Ref.[18]) There are several key points that may be drawn from Figs. 2-5. First is that between about 18 T and B_{th} SdH oscillations are observed at low temperatures even though R_{zz} exhibits a negative dR/dT in this activated region (Fig.1). Hence the sample is a quasi-two dimensional metal in this range. Second, the transition at B_{th} is highly hysteretic, and therefore first order. For fields above B_{th}, the inter-plane resistance R_{zz} increases by orders of magnitude, and in some cases becomes unmeasurable by conventional transport methods. B_{th} is temperature dependent, and moves to higher fields with increasing temperature. We note that the upper boundary of the high field phase in Fig. 1 approaches a value near T_a. Third, as Fig. 3 indicates, B_{th} is only weakly dependent on field orientation, and unlike the case for an orbital Fermi surface nesting effect, B_{th} actually reaches a minimum for in-plane magnetic field.

Before discussing the mechanism for this new high field state, it is instructive to consider some other details as-

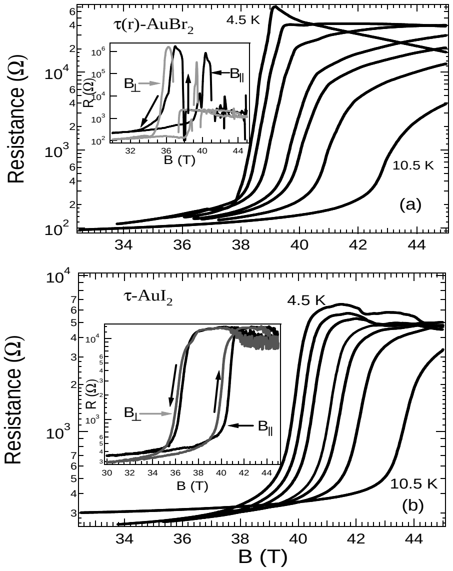

FIG. 3: Magnetoresistance studies of the high field transition in the τ-phase materials in the hybrid magnet for different temperatures (10.5 K, 9 K, 7.8 K, 7.1 K, 6.7 K, 5.6 K, 4.5 K). a) $\tau(r) - AuBr_2$, b) $\tau - AuI_2$. Insets: Magnetoresistance measurements for magnetic field parallel (gray-scale: θ=90^o) and perpendicular (solid black: θ = 0^o) to the conducting planes at T = 1.5 K.

sociated with the τ-phase materials. Even in the absence of magnetic field, these materials have the appearance of "bad metals". A simple evaluation of the carrier scattering time, based on either in-plane or inter-plane conductivity, over a broad temperature range, leads to a mean free path comparable to the unit cell dimensions (see also Ref. [19]). In marked contrast, for moderate magnetic fields where quantum oscillations (SdH) are observed, we find a Dingle temperature[18] of only 1.3 K which translates to a mean free path of about $60\mu m$. This difference is not easily reconciled based on any simple homogenous model. That the disorder may arise from the inter-plane sites comes from investigations of R_{zz} in tilted magnetic fields[18, 22] in τ-AuBr$_2$ which show no evidence for the "Yamaji effect"[13]. That is, no angular dependent magnetoresistance oscillations(AMRO) in R_{zz} associated with a finite inter-plane bandwidth and mean free path are observed. Hence the inter-planar coherence required for semi-classical trajectories on a warped cylindrical Fermi surface is not satisfied. Evidence for non-metallic behavior, coupled with the appearance of quantum oscillations in quasi-two dimensional metals are not without precedent, as recently reported in both organic[20, 21] and TMO[7] systems.

Evidence for weak ferromagnetism has been reported in the EDO class of τ-phase materials[23, 24, 25, 26, 27] where oxygen replaces the two nitrogen sites (N$_1$ and N$_2$ in Fig. 1) in the DMEDT-TTF donor. Since there

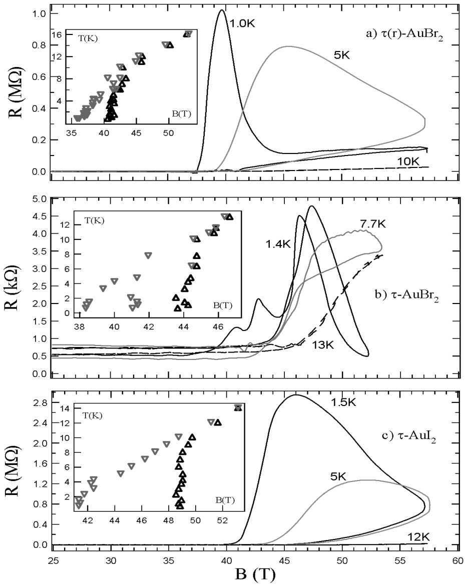

FIG. 4: Magnetoresistance studies of the high field transition in the τ-phase materials in pulsed magnetic fields. The loop-like hysteresis in the signal in the high field phase is due in part to the large RC time constants in the presence of a rapidly changing magnetic field. a) $\tau(r)$-AuBr$_2$, b) τ-AuBr$_2$, c) τ-AuI$_2$. Insets: hysteretic high field phase boundaries determined from linear extrapolation of the slope of dR_{zz}/dB (at the onset of the insulating phase) to the field axis. In τ-AuBr$_2$ SdH oscillations are apparent, as is some evidence for sub-phases, in the high field phase.

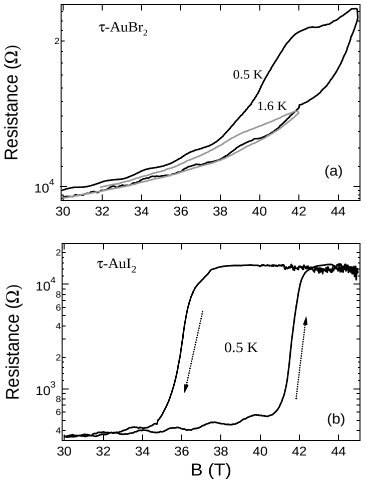

FIG. 5: The SdH signal in the vicinity of B_{th} for a) τ-AuBr$_2$ at T = 0.5 K up to 45 T, and T = 1.6 K up to 42 T), b) τ-AuI$_2$ at 0.5 K up to 45 T . (The SdH signal for $\tau(r)$-AuBr$_2$ has not yet been clearly observed.)

is no magnetic ion present, magnetism must arise either from the bands or from disorder (localized moments). Band magnetism has recently been treated by Arita et al.[28], based on consideration of the very flat, narrow ($E_F \approx 8meV$) bands that appear at the Fermi level from the tight binding calculations. Although magnetization studies have shown a small (0.001 μ_B/formula unit) moment, no hysteresis has been observed in magnetization data[26]. Recent far infrared measurements indicate that the methyl groups show disorder, and it has been suggested that this may lead to electronic localization and magnetism at low temperatures[29].

One final important detail is the relative constancy of the SdH oscillation frequency in the vicinity of B_{th}, which indicates that there is no catastrophic change in the quasi-two dimensional (Q2D) electronic structure. Rather, the SdH waveforms (which appear only below about 1.5 K due to the large effective mass[18]) remain observable until the resistance becomes forbiddingly large, either for increasing, or decreasing field through B_{th}. These effects are particularly evident in Figs. 4b and 5.

Based on the evidence above, we argue that the phenomena in the τ-phase materials is linked to the disorder in the donor and anion structure. The influence of high magnetic fields on this disorder drives the system into a state of highly de-coupled two dimensional Fermi liquid layers. This conclusion is supported by noting that B_{th} is the lowest in the most disordered (racemic) system. That the disorder, and the resulting incoherent transport is limited to the inter-planer layers, is evident from the presence of the SdH effect, and the absence (or attenuation) of semiclassical orbits (AMRO) in tilted magnetic fields. Hence it is unlikely that the mechanism that stabilizes the high field phase is a result of Fermi surface nesting, especially in light of the weak dependence of B_{th} on magnetic field direction. When the field is aligned in-plane, B_{th} actually reaches a minimum, and this may be due to further compression of the Q2D electron wave function expected for a quasi-two-dimensional conductor in this configuration.

A remaining question is how the magnetic field couples to the inter-planar disorder, and we may speculate about two possibilities. The first is simply through localized spins, where in the low field phase, magnetic polarization may reduce carrier scattering. This would give a negative magnetoresistance and allow the SdH effect to eventually appear. In the high field phase, magnetic order may set in, thereby making the inter-layer transport incoherent due to first order, domain-like structures. A second possibility may be diamagnetic in origin, arising from non-stoichiometric sites in the inter-layer anion structure. The high magnetic fields needed to cross B_{th}, and the linear shape of the anions make (normally weak) diamagnetic processes, that may alter the inter-layer structure, more probable. Either mechanism should be roughly isotropic with respect to magnetic field direction.

In summary, the similarities between organic molecular solids and the metal oxides (cuprates, manganites, ruthenates, etc.) continues to be the subject of general interest in materials science. These relationships may be even closer, as evidenced from the results presented in this Letter. Here, superimposed on the "conventional" picture of a quasi-two dimensional Fermi surface, we find evidence for phase transitions driven by disorder and magnetism.

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[1] For a review see E. Dagotto, T. Hotta, and A. Moreo, Phys. Rep. **344**, 1 (2001).

[2] Y. Tokura and Y. Tomioka, J. Mag. Mag. Mat. **200**, 1(1999).

[3] U. Welp *et al.*, Phys. Rev. Lett. **69**, 840(1992).

[4] Y.V. Sushko *et al.*, J. Superconductivity, **7**, 937(1994).

[5] R.H. McKenzie, Science, **278**, 820(1997).

[6] E. Dagotto, Science, **293**, 2410(2001).

[7] G. Cao *et al.*, Bull. Am. Phys. Soc. **47**, 912(2002).

[8] G. C. Papavassiliou et al., Organic Superconductivity (Plenum Press, New York, 1990).

[9] A. Terzis *et al.*, Synth. Met. **42**, 1715 (1991).

[10] J. S. Zambounis *et al.*, Solid State Commun. **95**, 211 (1995).

[11] G. C. Papavassiliou *et al.*, Synthetic Metals **70**, 787 (1995).

[12] G. C. Papavassiliou *et al.*, Mol. Cryst. Liq. Cryst. **83**, 285 (1996).

[13] T.Ishiguro, K. Yamaji, and G. Saito, Organic Superconductors II (Springer-Verlag, Berlin, Heidelberg, New York, 1998).

[14] T. Osada, H. Nose, M. Kuraguchi, Physica B **294-295**, 402(2001).

[15] J. M. Williams *et al.*, *Organic Superconductors (including Fullerenes)*, Prentice-Hall, Englewoods Cliffs, New Jersey (1992).

[16] G. C. Papavassiliou *et al.*, Synth. Met. **120**, 743 (2001).

[17] G.C. Papavassiliou, A. Terzis, and C. P. Raptopoulou, Naturforsch. **56b** , 963(2001).

[18] K. Storr *et al.*, Phys. Rev. B **64**, 045107/1 (2001).

[19] N. A. Fortune et al., Mat. Res. Soc. Symp. Proc. **328**, 307(1994).

[20] L. Balicas *et al.*, Phys. Rev. Lett. **87**, 067002(2001).

[21] J. Wosnitza *et al.*, Phys. Rev. Lett. **86**, 508(2001).

[22] J. S. Brooks *et al.*, Mol. Cryst. Liq. Cryst. , in press, and cond-mat/0012291(2002).

[23] K. Murata *et al.*, Synthetic Metals **86**, 2021 (1997).

[24] H. Yoshino *et al.*, J. Phys. Soc. Japan **66**, 2410 (1997).

[25] H. Yoshino *et al.*, J. Phys. Soc. Japan **68**, 177 (1999).

[26] K. Konoike *et al.*, Synth. Met. **120**(1-3),801(2001).

[27] T. Konoike *et al.*, J. Phys. Chem. Solids in press (2002).

[28] R. Arita, K. Kuroki, and H. Aoki, Phys. Rev. B **61**, 3207 (2000).

[29] I. Olejniczak *et al.*, Phys. Rev. B **62** 15634(2000).